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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Confirmation No.: 6104

Wen-Fang LEE, et al.

Examiner: C. Chaudhari

Serial No.: 10/660,606

Art Unit: 2813

Filed: September 12, 2003

Docket No.: 030108

For: METHOD AND STRUCTURE TO IMPROVE THE GATE COUPLING RATIO
(CGR) FOR MANUFACTURING A FLASH MEMORY DEVICE

RESPONSE TO THE RESTRICTION REQUIREMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

November 15, 2004
(November 13, 2004 = Saturday)

Sir:

In response to the Restriction Requirement dated October 13, 2004, Applicants hereby elect to prosecute Group I, Claims 1-17, (drawn to a method of making a semiconductor device, classified in class 438, subclass 257) without traverse. Applicants reserve the right to file a divisional application directed to non-elected claims.

If any additional fees are due with regard to this paper, please charge counsel's Deposit Account No. 50-2394.

Respectfully submitted,

IPS, Inc.

A handwritten signature in black ink that reads "Robert J. Forsell, Jr." followed by a stylized signature.

Robert J. Forsell, Jr.
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